

DEFECTS IN MATERIALS

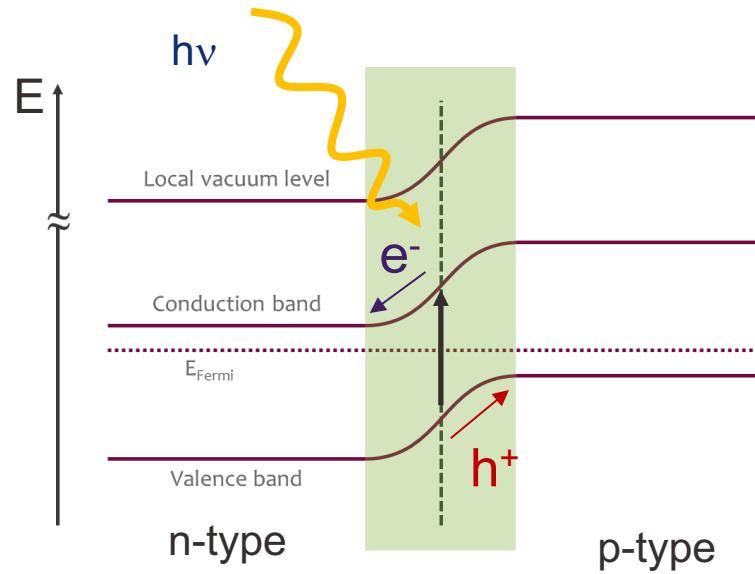
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Ethiopian Physics Society of North America
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McCORMICK SCHOOL OF
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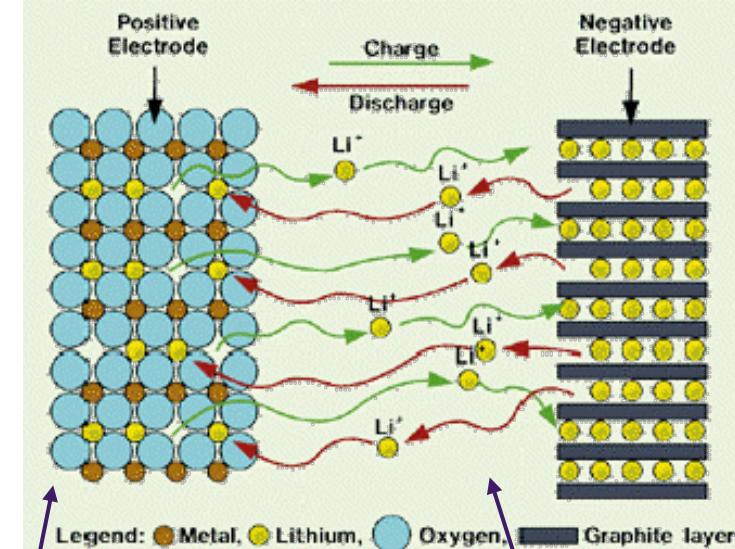
Point Defects in Non-metals

Photovoltaics



Semiconductors

Batteries



Electrolyte (ionic conductor)

Mixed ionic and electronic conductor (MIEC)

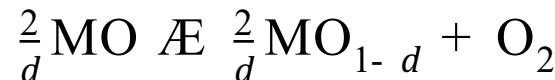
Lecture Outline

Thermodynamics of defect formation

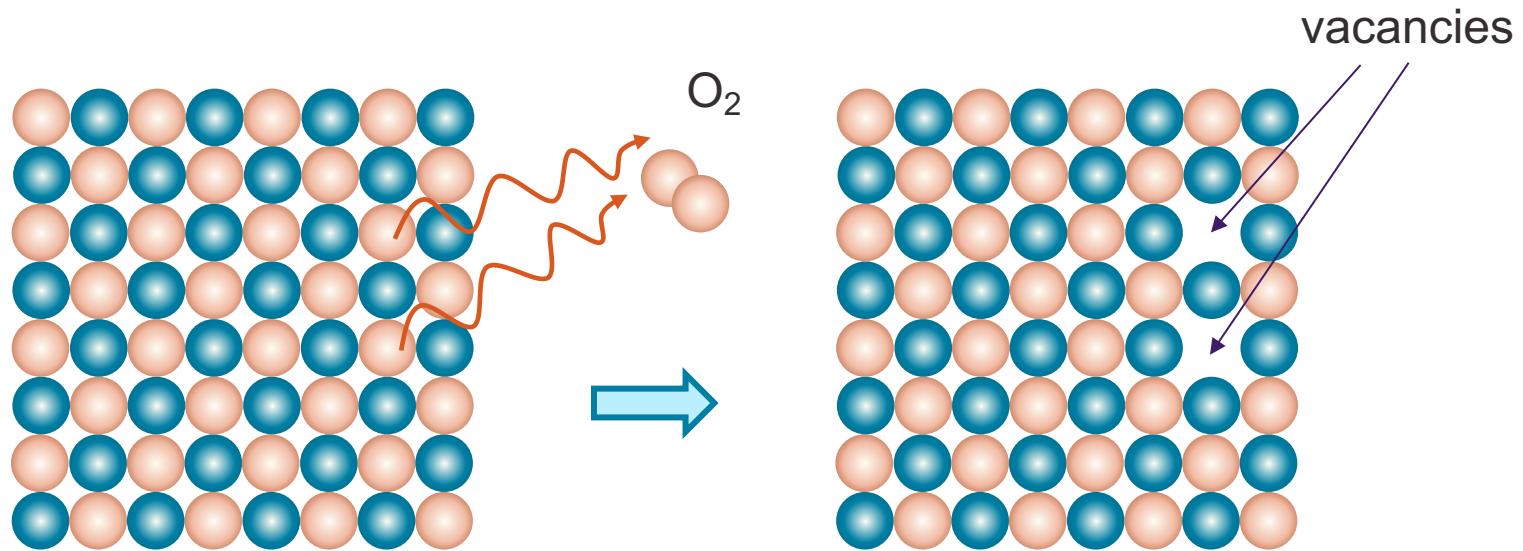
- ➡ • Macroscopic thermodynamic approach
 - Gas and solid state in equilibrium
 - Experimental methods
- Microscopic thermodynamics
 - Reduction/oxidation reaction
- Microscopic point defects
 - Energetics of defect formation
- Brouwer diagrams – Defect concentrations

Point Defect Formation: a Chemical Reaction

Partial reduction of a variable valence oxide



$\delta = \text{oxygen nonstoichiometry}$

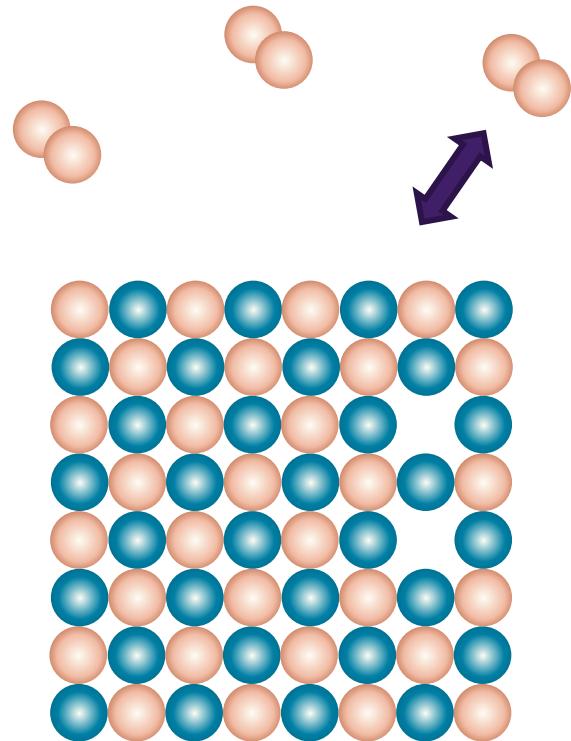


1. What is the nature of the defects that result from oxygen loss?
2. In fact, we don't need to know the answer in order to measure the thermodynamics.



Macroscopic Thermodynamic Description

oxygen in the gas phase



oxygen in the solid phase

Equilibrium:

$$\mu_O(\text{sol}) = \mu_O(\text{gas}) \quad \text{chemical potential of oxygen}$$

$\mu_O(\text{gas})$ is directly given by oxygen partial pressure in the gas phase

Ideal gas:

at reference pressure

$$\mu_O(T) = \mu_O^0(T) + RT \ln\left(\hat{p}_{O_2}^{1/2}\right)$$

$$\hat{p}_{O_2} = p_{O_2} / p_{O_2}^{\text{ref}}$$

Goal: measure δ at known \hat{p}_{O_2}

$\delta(T, \hat{p}_{O_2})$ reflects thermodynamics of defect formation

Macroscopic Thermodynamic Description

Gibbs (free) energy

$$G(T, P, \{n_j\}) = H - TS$$

↑ ↑
enthalpy entropy

chemical potential

$$\left. \frac{\partial G}{\partial n_i} \right)_{P, T, n_{j \neq i}} = \mu_i \equiv \bar{G}_i \quad \begin{matrix} \text{partial molar} \\ \text{Gibbs energy} \end{matrix}$$

or use lower case

$$\Rightarrow \mu_i = \bar{H}_i - T\bar{S}_i \quad \mu_i = h_i - Ts_i$$

partial molar enthalpy partial molar entropy

$$\mu_O(T) = \mu_O^0(T) + RT \ln(\hat{p}_{O_2}^{1/2})$$

relative chemical potential

$$\mu_O(T) - \mu_O^0(T) = \Delta\bar{G}_O^0 = RT \ln(\hat{p}_{O_2}^{1/2}) = \Delta\bar{H}_O^0 - T\Delta\bar{S}_O^0$$

relative partial molar
enthalpy and entropy

relative partial molar Gibbs energy

these G , H and S terms are functions of δ in $MO_{1-\delta}$

Macroscopic Thermodynamic Description

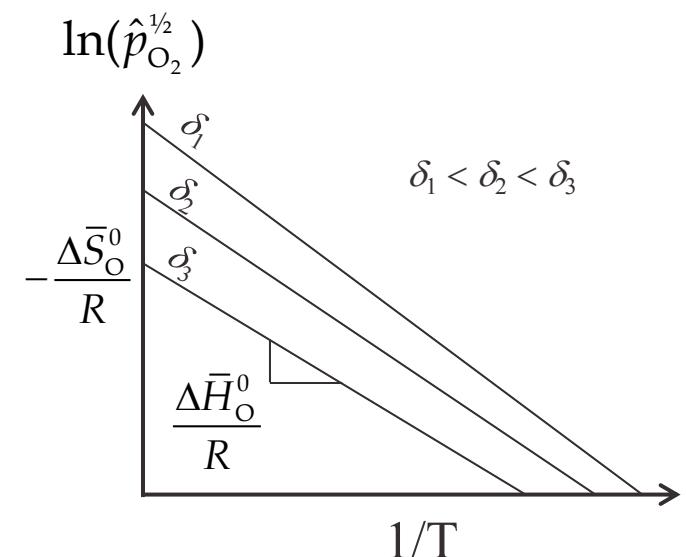
$$\Delta\mu_O^0 = \Delta\bar{H}_O^0 - T\Delta\bar{S}_O^0 = RT \ln(\hat{p}_{O_2}^{1/2}) \quad \leftarrow \text{ terms depend on } \delta$$

Enthalpy $\frac{\Delta\mu_O^0}{T} = \frac{\Delta\bar{H}_O^0}{T} - \Delta\bar{S}_O^0 \quad \frac{\partial(\Delta\mu_O^0/T)}{\partial(1/T)} = \Delta\bar{H}_O^0 \quad \Delta\bar{H}_O^0 = \frac{1}{2}R \frac{\partial \ln(\hat{p}_{O_2})}{\partial(1/T)}$

Entropy $\frac{\partial\Delta\mu_O^0}{\partial T} = -\Delta\bar{S}_O^0 \quad \Delta\bar{S}_O^0 = -\frac{1}{2}R \frac{\partial T \ln(\hat{p}_{O_2})}{\partial T}$

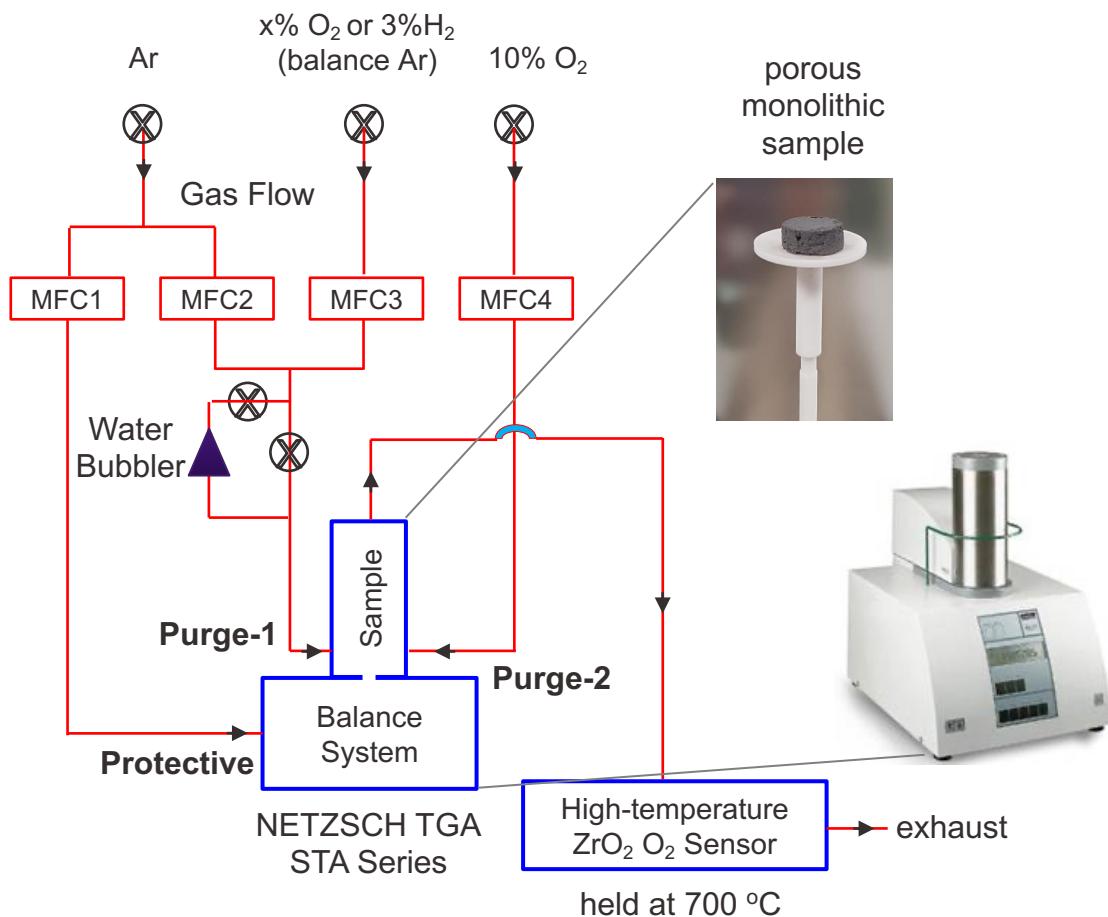
Both from one plot $\ln(\hat{p}_{O_2}^{1/2}) = \frac{\Delta\bar{H}_O^0}{RT} - \frac{\Delta\bar{S}_O^0}{R}$

Nonlinearity from heat capacity effects, or
temperature induced change in defect chemistry

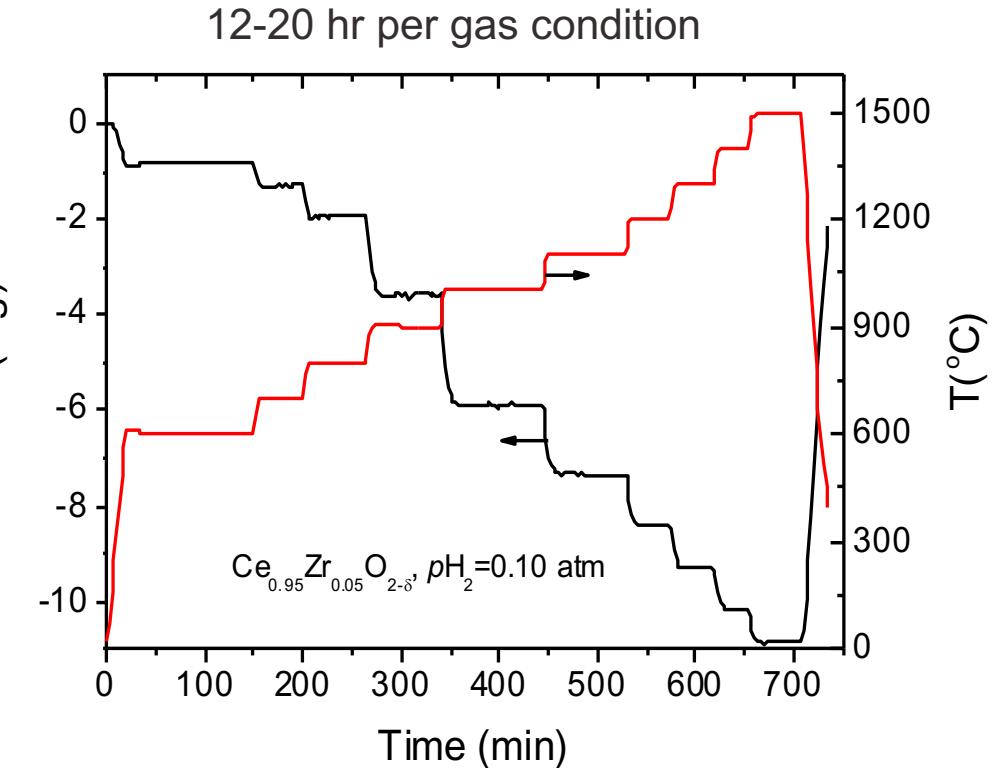


Measuring Thermodynamics of Defect Formation

Goal: measure δ at known \hat{p}_{O_2}



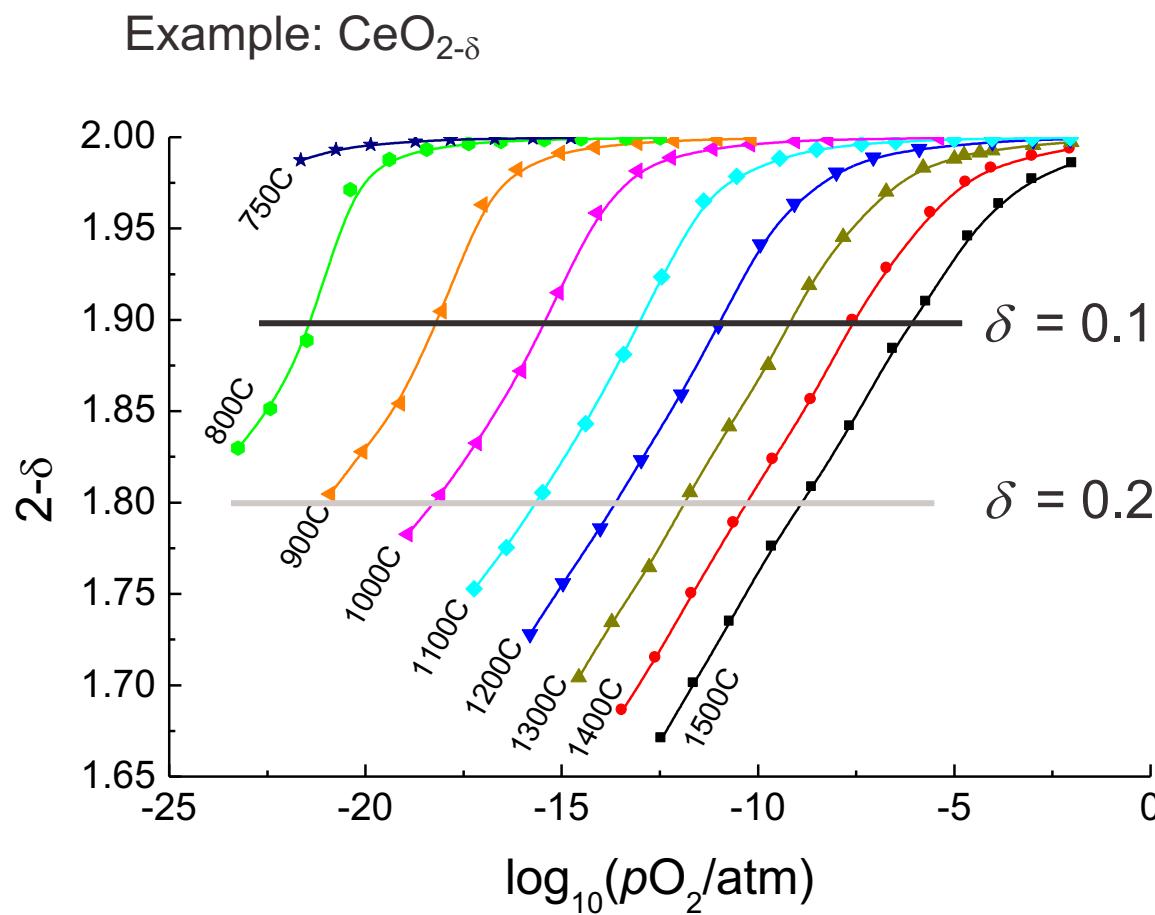
Mass as a function of T under various gases



- Moderate pO_2 : O₂/Ar mixtures
- Low pO_2 : H₂O/H₂/Ar mixtures

Establishing Thermodynamic Functions

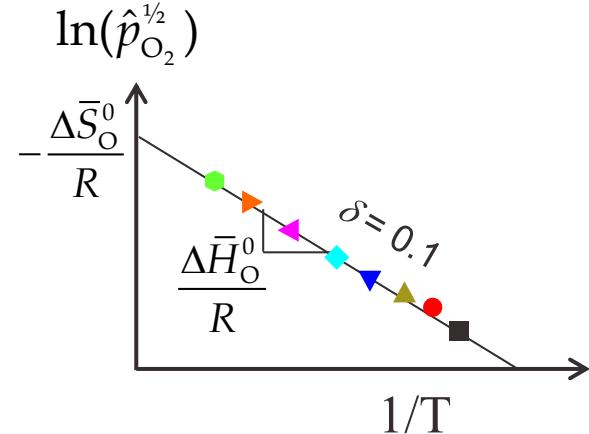
$$\mu_O(T) - \mu_O^0(T) = \Delta\bar{G}_O^0 = RT \ln(\hat{p}_{O_2}^{1/2}(\delta)) = \Delta\bar{H}(δ)_O^0 - T\Delta\bar{S}(δ)_O^0$$



$$\ln(\hat{p}_{O_2}^{1/2}) = \frac{\Delta\bar{H}_O^0}{RT} - \frac{\Delta\bar{S}_O^0}{R}$$

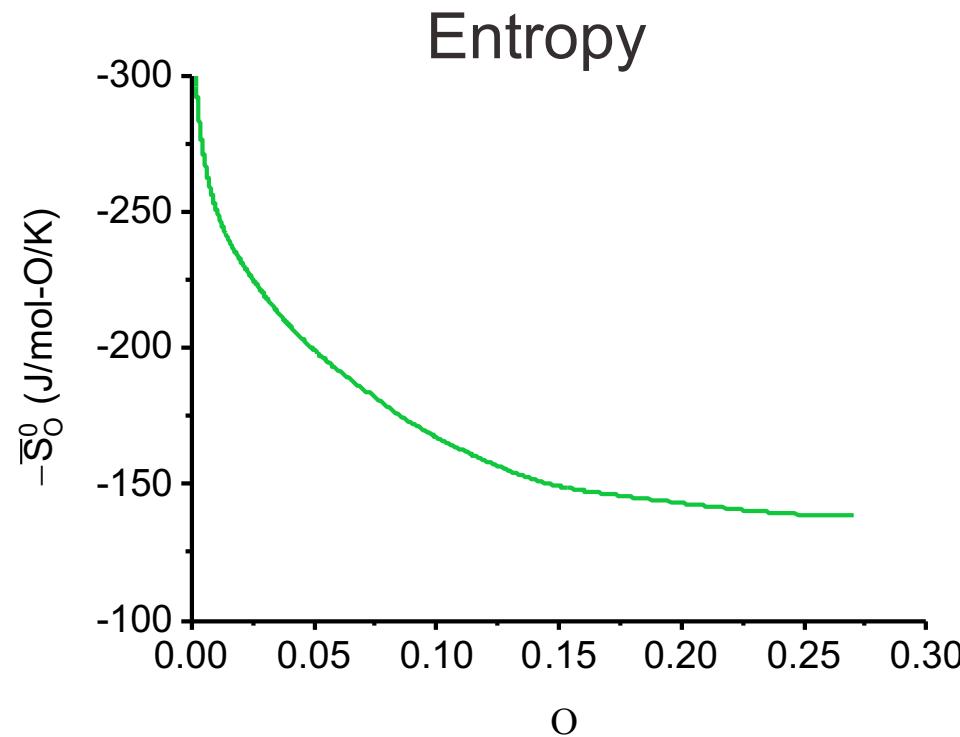
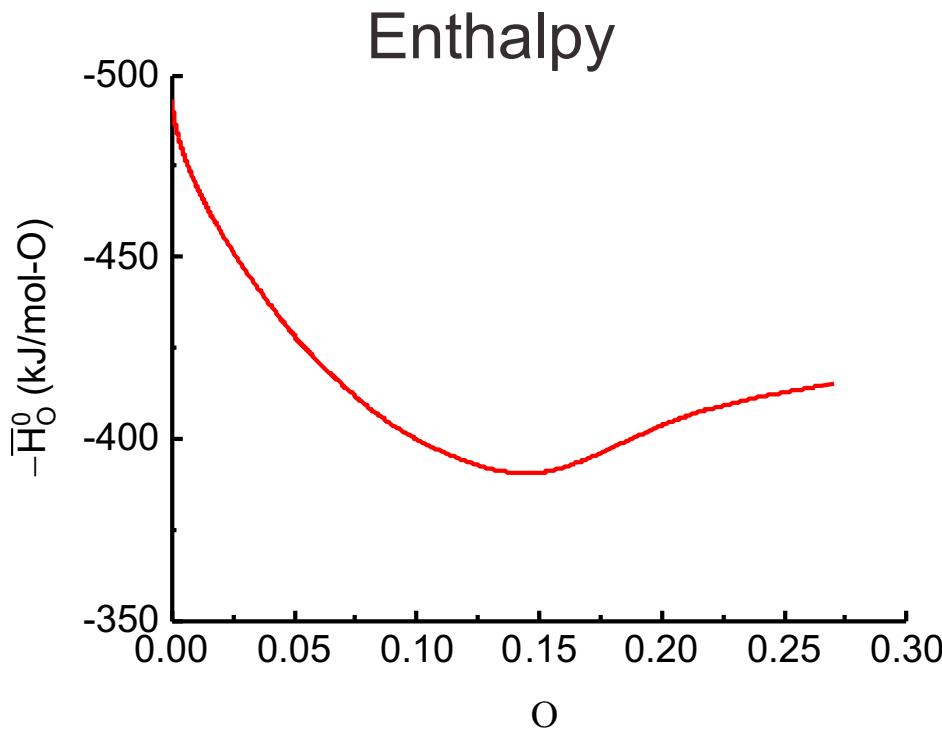
$T, ^\circ\text{C}$	pO_2, atm
800	10^{-23}
900	10^{-19}
1000	10^{-16}
1100	etc.

conditions for $\text{CeO}_{1.9}$



another set for $\text{CeO}_{1.8}$, etc.

Thermodynamic Functions



Value?

$$\text{Invert } \ln(\hat{p}_{O_2}^{1/2}) = \frac{\Delta\bar{H}_O^0}{RT} - \frac{\Delta\bar{S}_O^0}{R}$$

to solve for δ at given T and \hat{p}_{O_2}

Insight into chemical and physical nature of defects from functional forms of H and S

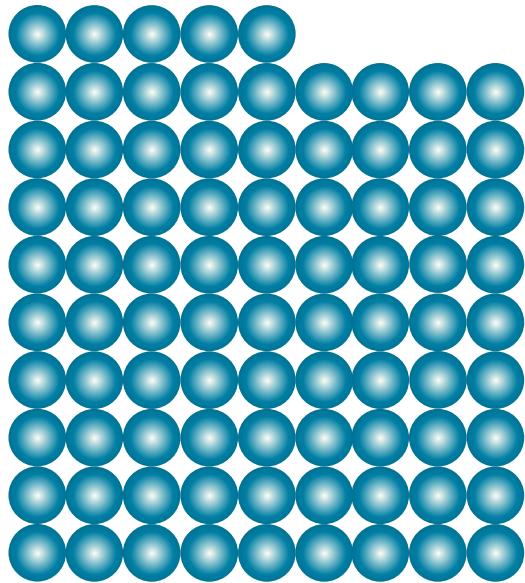
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Thermodynamics of defect formation

- Macroscopic thermodynamic approach
 - Gas and solid state in equilibrium
 - Experimental methods
- • Microscopic thermodynamics
 - Reduction/oxidation reaction
- Microscopic point defects
 - Energetics of defect formation
- Brouwer diagrams – Defect concentrations

Microscopic Thermodynamic Description

Equilibrium: minimize G of the system



Vacancies in metals

$$G - G_0 = \Delta G = \Delta H_{vac} - T \Delta S_{vac} \quad N_{vac} = \text{moles of vacancies}$$

↑
no vacancies
with vacancies

$$\Delta G = N_{vac} (\Delta h_{f,vac} - T \Delta s_{f,vac}^{non-config}) - T S_{vac}^{config}$$

non-interacting (dilute limit)
"excess" entropy

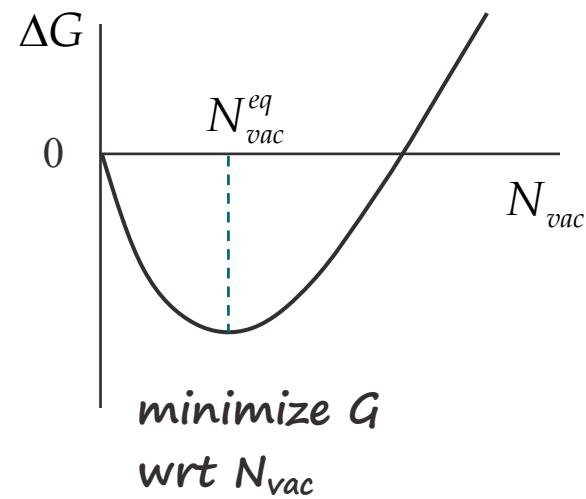
$$S_{vac}^{config} = R \ln \Omega \quad \text{not directly proportional to } N_{vac}$$

$$\Delta G = N_{vac} (\Delta h_{f,vac} - T \Delta s_{f,vac}^{non-config}) + RT \left[N_{vac} \ln \left(\frac{N_{vac}}{N_A + N_{vac}} \right) + N_A \ln \left(\frac{N_A}{N_A + N_{vac}} \right) \right]$$

non-interacting, randomly distributed vacancies

Point Defect Concentration in Metals

$$\Delta G = N_{vac} (\Delta h_{f,vac} - T \Delta s_{f,vac}^{non-config}) + RT \left[N_{vac} \ln \left(\frac{N_{vac}}{N_A + N_{vac}} \right) + N_A \ln \left(\frac{N_A}{N_A + N_{vac}} \right) \right]$$



$$\Rightarrow \mu_{vac} = 0$$

$$\frac{\partial \Delta G}{\partial N_{vac}} = \frac{\partial G}{\partial N_{vac}} = \Delta h_{f,vac} - T \Delta s_{f,vac}^{non-config} + RT \ln \left(\frac{N_{vac}}{N_A + N_{vac}} \right) = 0$$

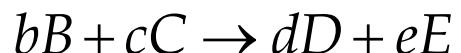
fractional concentration

χ_{vac}

$$\Rightarrow \chi_{vac} = \exp \left(\underbrace{\frac{-\left(\Delta h_{f,vac} - T \Delta s_{f,vac}^{non-config} \right)}{RT}}_{\Delta g'_{f,vac}} \right) = \exp \left(\frac{-\left(\Delta g'_{f,vac} \right)}{RT} \right)$$

Defect Formation as a Chemical Reaction

Generic reaction



Equilibrium:

$$\sum_i^{prod} v_i \mu_i = \sum_j^{react} v_j \mu_j$$

in the state of interest

$$\mu_i = \mu_i^0 + RT \ln a_i$$

in the reference state

ideal gas

$$\mu(T) = \underbrace{\mu(T, p^0)}_{\text{standard pressure}} + RT \ln \left(\frac{p}{p^0} \right)$$

dilute component

$$\mu(T) = \underbrace{\mu(T, \text{pure})}_{\text{standard concentration}} + RT \ln \left(\frac{n}{n_{\text{pure}}} \right)$$

Equilibrium:

$$\underbrace{\sum_i^{prod} v_i \mu_i^0 - \sum_j^{react} v_j \mu_j^0}_{\Delta_{rxn} g^0} = -RT \ln \left(\frac{a_{p1}^{v_{p1}} a_{p2}^{v_{p2}} a_{p3}^{v_{p3}} \dots}{a_{r1}^{v_{r1}} a_{r2}^{v_{r2}} a_{r3}^{v_{r3}} \dots} \right)$$

products

reactants

$$Q = \left(\frac{a_{p1}^{v_{p1}} a_{p2}^{v_{p2}} a_{p3}^{v_{p3}} \dots}{a_{r1}^{v_{r1}} a_{r2}^{v_{r2}} a_{r3}^{v_{r3}} \dots} \right)$$

Equilibrium:

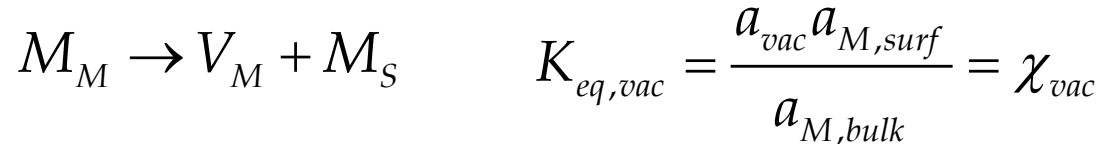
$$\left(\frac{a_{p1}^{v_{p1}} a_{p2}^{v_{p2}} a_{p3}^{v_{p3}} \dots}{a_{r1}^{v_{r1}} a_{r2}^{v_{r2}} a_{r3}^{v_{r3}} \dots} \right) = \exp \left(\frac{-\Delta_{rxn} g^0}{RT} \right) = K_{eq}$$

Vacancy Formation Reaction in Metals

Minimization of G , considering configurational entropy gave

$$\chi_{vac} = \exp\left(\frac{-\left(\Delta h_{f,vac} - T\Delta s_{f,vac}^{non-config}\right)}{RT}\right) = \exp\left(\frac{-\left(\Delta g'_{f,vac}\right)}{RT}\right)$$

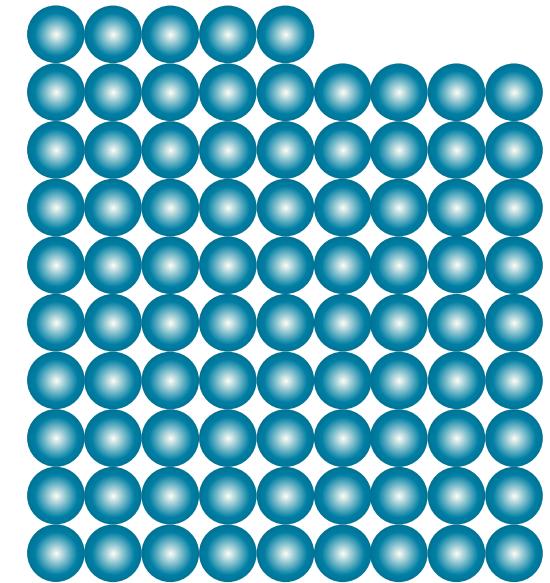
Treat as
defect reaction



$$K_{eq,vac} \equiv \exp\left(\frac{-\left(\Delta_{rxn}g^0\right)}{RT}\right) \Rightarrow \Delta_{rxn}g^0 = \Delta h_{f,vac} - T\Delta s_{f,vac}^{non-config}$$

$$\Delta_{rxn}g^0 = \Delta_{rxn}h^0 - T\Delta_{rxn}s^0$$

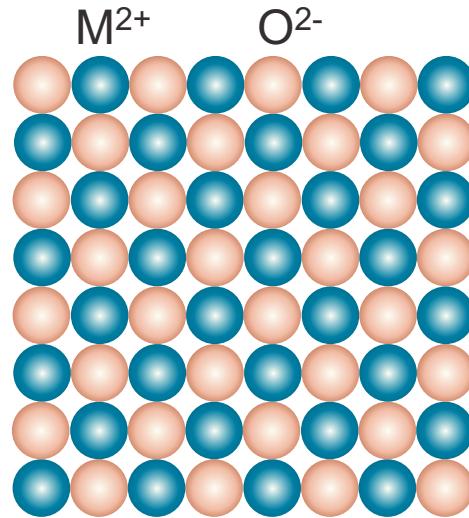
$$\Delta_{rxn}g^0 = \sum_i^{prod} v_i \mu_i^0 - \sum_j^{react} v_j \mu_j^0 = \mu_{vac}^0$$



Note that the standard Gibbs energy of reaction does not include solid state configurational entropy

Microscopic Defect formation in Metal Oxide

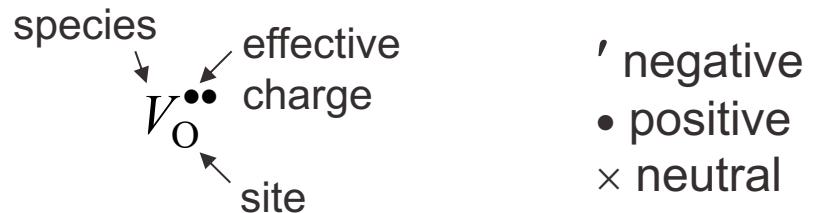
Define the point defects involved in the reaction



Vacancies created at oxygen ion sites
O²⁻ ions must be removed as neutral species
Electrons have to be ‘placed’ somewhere:

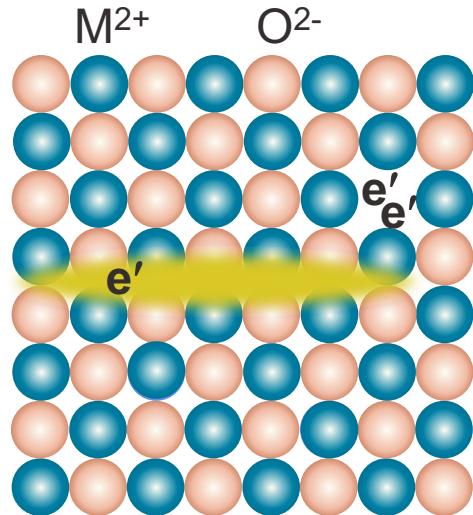
1. Electrons trapped at vacancies
2. M²⁺ reduced to M⁺, electrons trapped at metal sites
3. Electrons added to the conduction band, itinerant electrons

Describe using formal defect notation:

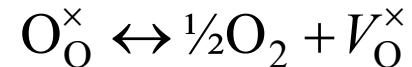


Microscopic Defect formation in Metal Oxide

Define the point defects involved in the reaction



1. Electrons trapped at vacancies

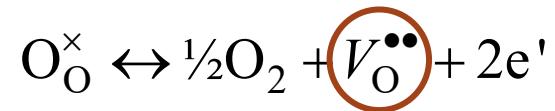


charged defects

2. M²⁺ reduced to M⁺, electrons trapped at metal sites



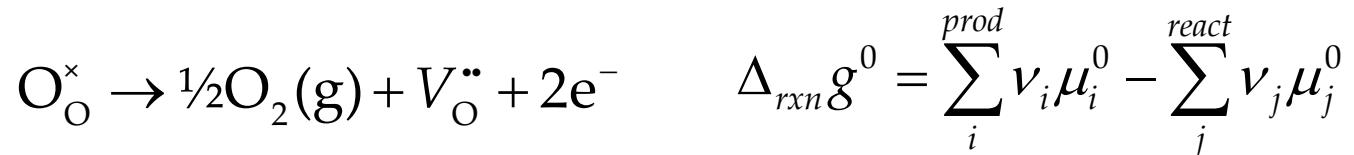
3. Electrons added to the conduction band, itinerant electrons



Reactions obey charge, site, and mass balance

'Isolated' charged defect formation impacts electron count: $\text{M}_\text{M}^\times + e' \leftrightarrow \text{M}'_\text{M}$

Consider Electrons in Conduction Band



$$\Delta_{red}g^0 = \frac{1}{2}\mu_{\text{O}_2}^0 + \mu_{\text{V}_\text{O}^\bullet}^0 + 2\mu_{\text{e}^-}^0 - \mu_{\text{O}_\text{O}^\times}^0 = -RT \ln \left(\frac{a_{\text{O}_2}^{\frac{1}{2}} a_{\text{V}_\text{O}^\bullet} a_{\text{e}^-}^2}{a_{\text{O}_\text{O}^\times}} \right) \approx -RT \ln \left(\hat{p}_{\text{O}_2}^{\frac{1}{2}} \chi_{\text{V}_\text{O}^\bullet} \chi_{\text{e}^-}^2 \right)$$

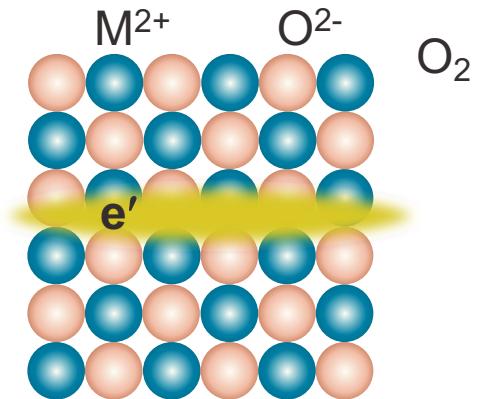
$$-\Delta_{red}g^0 = \underline{RT \ln(\hat{p}_{\text{O}_2}^{\frac{1}{2}})} + RT \ln(\chi_{\text{V}_\text{O}^\bullet} \chi_{\text{e}^-}^2)$$

relative partial molar quantities

$$\text{Recall: } \mu_\text{O} = \mu_\text{O}^0 + RT \ln(\hat{p}_{\text{O}_2}^{\frac{1}{2}}) \Rightarrow RT \ln(\hat{p}_{\text{O}_2}^{\frac{1}{2}}) = \mu_\text{O} - \mu_\text{O}^0 = h_\text{O} - h_\text{O}^0 - T(s_\text{O} - s_\text{O}^0) = \underline{\Delta \bar{H}_\text{O}^0 - T \Delta \bar{S}_\text{O}^0}$$

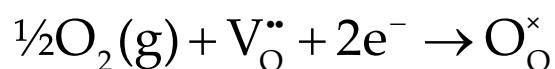
partial molar configurational entropy on removing O

$$-\Delta_{red}g^0 = \Delta \bar{H}_\text{O}^0 - T \Delta \bar{S}_\text{O}^0 + RT \ln(\chi_{\text{V}_\text{O}^\bullet} \chi_{\text{e}^-}^2) = \underbrace{\Delta \bar{H}_\text{O}^0}_{-\Delta_{red}h^0} - T \left(\underbrace{\Delta \bar{S}_\text{O}^0 - R \ln(\chi_{\text{V}_\text{O}^\bullet} \chi_{\text{e}^-}^2)}_{-\Delta_{red}s^0} \right) \quad \begin{array}{l} \text{for } \textbf{reduction} \text{ reaction} \\ \text{oxidation has opposite sign} \end{array}$$



Contributions to Thermodynamic Terms

Treat **oxidation** for sanity's sake



$$\Delta_{rxn}g^0 = \sum_i^{prod} v_i \mu_i^0 - \sum_j^{react} v_j \mu_j^0$$

$$\Delta_{oxd}g^0 = \mu_{\text{O}_{\text{O}}^{\times}}^0 - \mu_{\text{V}_{\text{O}}^{\cdot\cdot}}^0 - 2\mu_{\text{e}^-}^0 - \frac{1}{2}\mu_{\text{O}_2}^0$$

$$\Delta_{oxd}h^0 = \Delta\bar{H}_{\text{O}}^0$$

$$\Delta_{oxd}s^0 = \Delta\bar{S}_{\text{O}}^0 - R \ln(\chi_{\text{V}_{\text{O}}^{\cdot\cdot}} \chi_{\text{e}^-}^2)$$

configurational entropy change

$$\bar{S}_{oxd, config} < 0$$

$$\Delta_{oxd}h^0 = h_{\text{O}_{\text{O}}^{\times}}^0 - h_{\text{V}_{\text{O}}^{\cdot\cdot}}^0 - 2h_{\text{e}^-}^0 - \frac{1}{2}h_{\text{O}_2}^0$$

$$\Delta_{oxd}s^0 = \underbrace{s_{\text{O}_{\text{O}}^{\times}}^0 - s_{\text{V}_{\text{O}}^{\cdot\cdot}}^0 - 2s_{\text{e}^-}^0}_{\text{"excess" entropy in the solid (vibrational, electronic, magnetic)}} - \frac{1}{2}s_{\text{O}_2}^0$$

entropy of gas phase oxygen (large)

"excess" entropy in the solid
(vibrational, electronic, magnetic)

$$\Delta_{oxd}\bar{S}_{non-config}^0$$

Recall, we measure

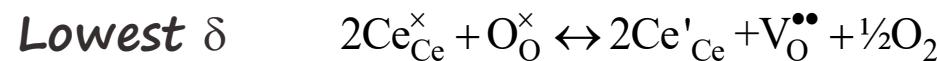
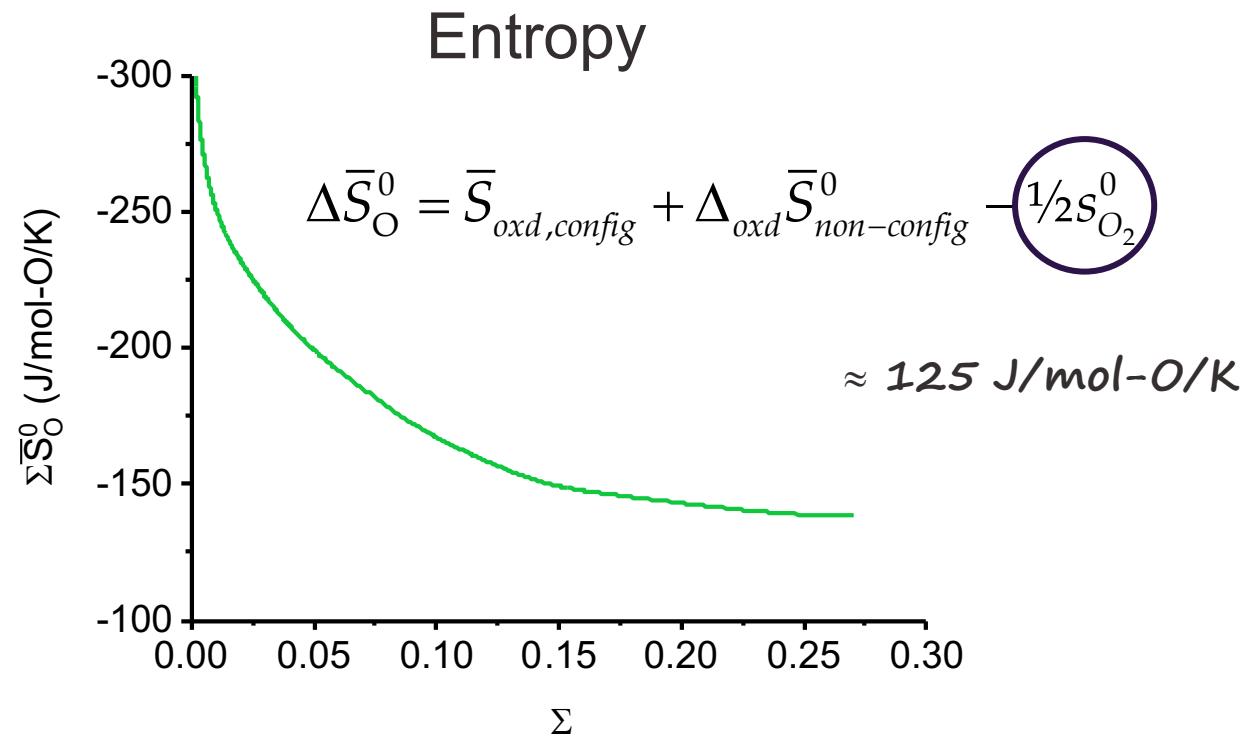
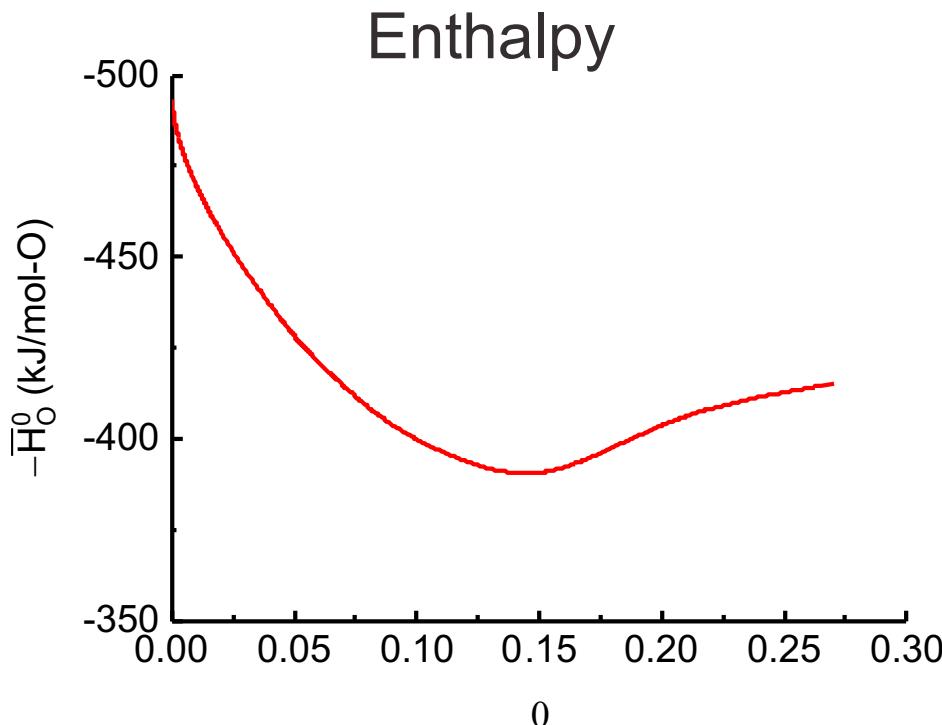
Partial molar enthalpy of oxygen

$$\Delta\bar{H}_{\text{O}}^0 = h_{\text{O}_{\text{O}}^{\times}}^0 - h_{\text{V}_{\text{O}}^{\cdot\cdot}}^0 - 2h_{\text{e}^-}^0 - \frac{1}{2}h_{\text{O}_2}^0$$

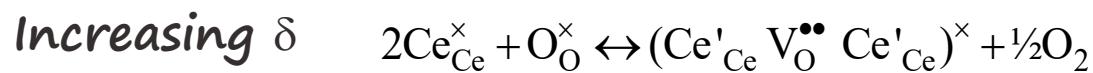
Partial molar entropy of oxygen

$$\Delta\bar{S}_{\text{O}}^0 = \Delta_{oxd}\bar{S}_{non-config}^0 - \frac{1}{2}s_{\text{O}_2}^0 + \bar{S}_{oxd, config}$$

Thermodynamic Functions



Dominated by large S of gas phase oxygen



Report: $\Delta \bar{S}_O^0 + \frac{1}{2} S_{O_2}^0 = \bar{S}_{oxd, config} + \Delta_{oxd} \bar{S}_{non-config}^0$

Configurational Entropy*

Depends on nature of reaction

$$\bar{S}_{config} = -R \ln \left(\frac{\chi_{p1}^{\nu_{p1}} \chi_{p2}^{\nu_{p2}} \chi_{p3}^{\nu_{p3}} \dots}{\chi_{r1}^{\nu_{r1}} \chi_{r2}^{\nu_{r2}} \chi_{r3}^{\nu_{r3}} \dots} \right)$$

tends to $-\infty$ as $\rightarrow 0$

1. Electrons trapped at vacancies



$$\bar{S}_{config}$$

neutrality constraint

$$\bar{S}_{config}$$

2. M^{2+} reduced to M^+ , electrons trapped at metal sites



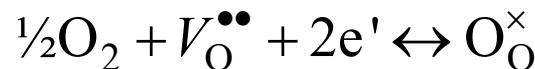
$$R \ln(\chi_{V_{\text{O}}^{\times}})$$

N/A

$$\sim R \ln(\delta)$$


$$R \ln \left(\frac{\delta}{2-\delta} \right)$$

3. Electrons added to the conduction band, itinerant electrons



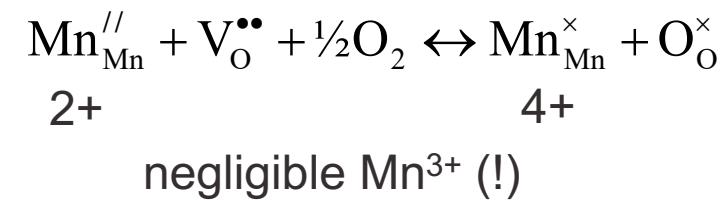
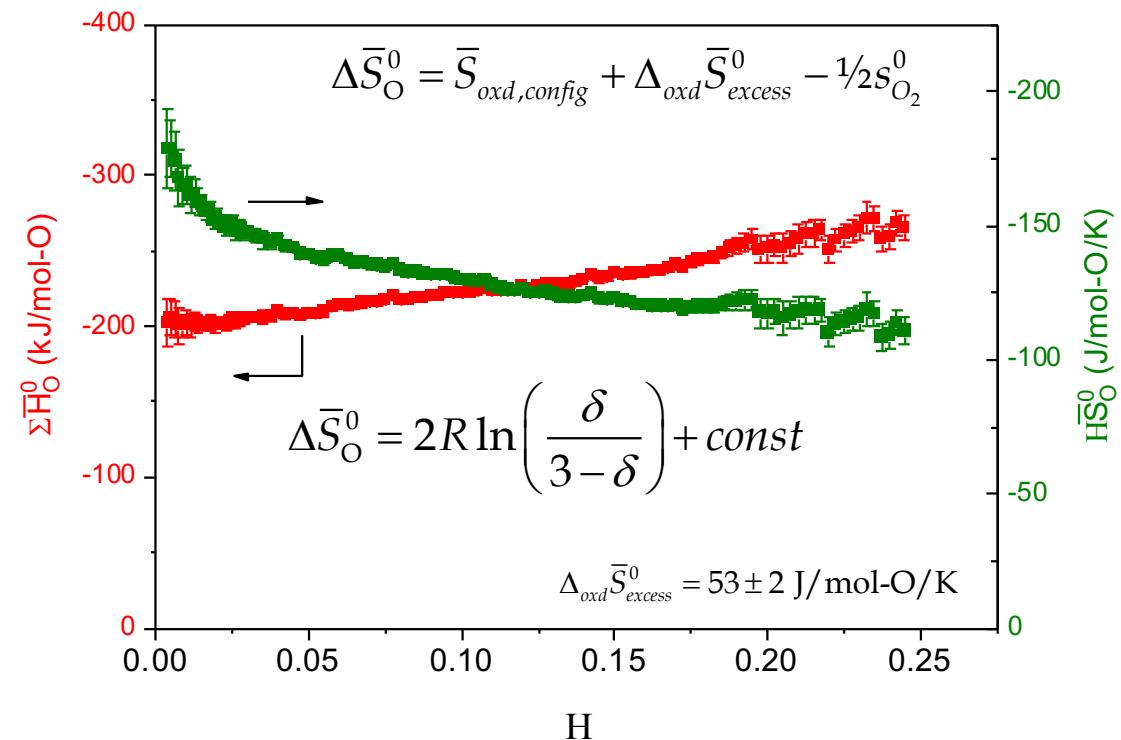
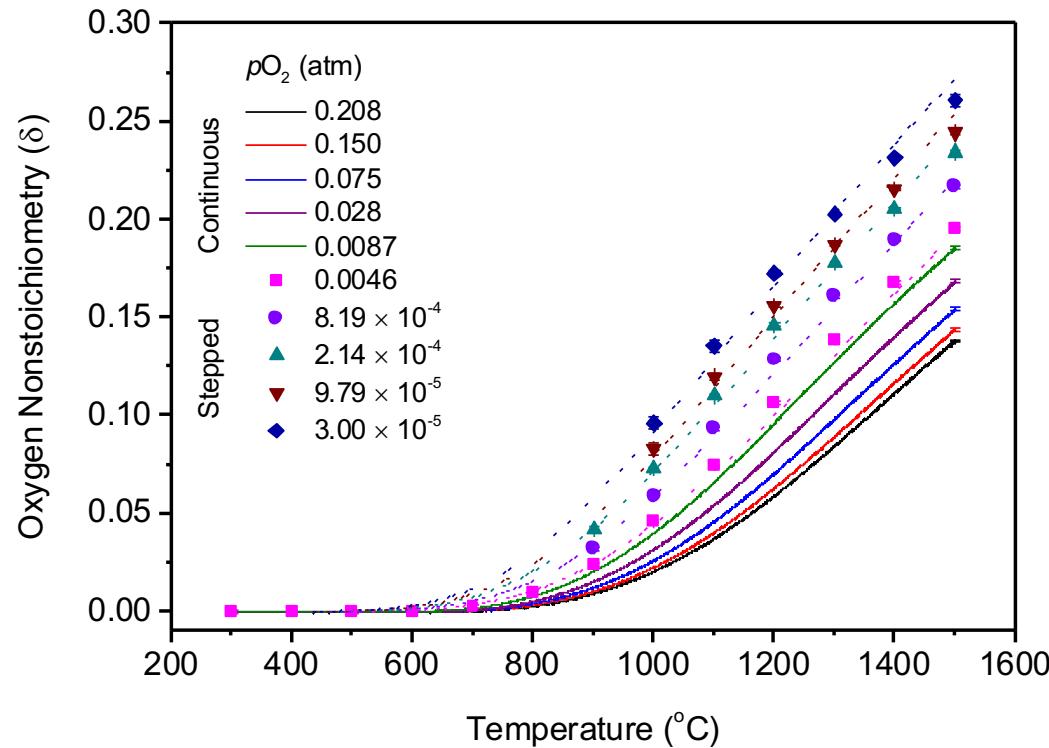
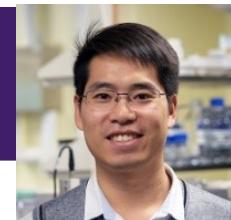
$$R \ln(\chi_{V_{\text{O}}^{\times}} \chi_{e^-}^2)$$

$$\chi_{V_{\text{O}}^{\bullet\bullet}} \propto \chi_{e^-}$$

$$\sim 3R \ln(\delta)$$

At large δ , need to include concentration of product in the quotient

Example: Sr(Ti_{0.5}Mn_{0.5})O_{3-δ}



Lecture Outline

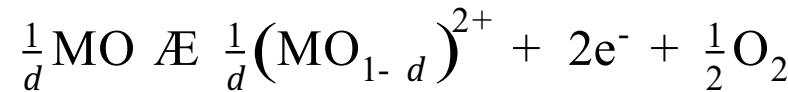
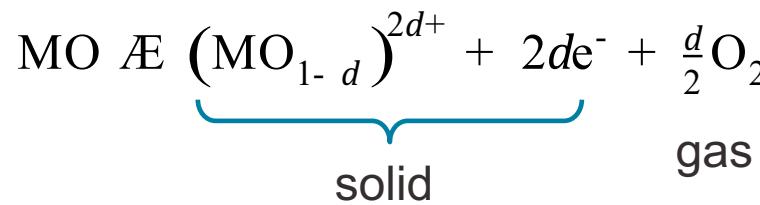
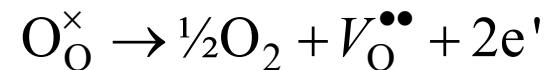
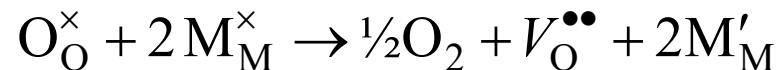
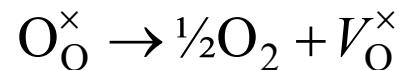
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- • Microscopic point defects
 - Energetics of defect formation
- Brouwer diagrams – Defect concentrations

Energetics



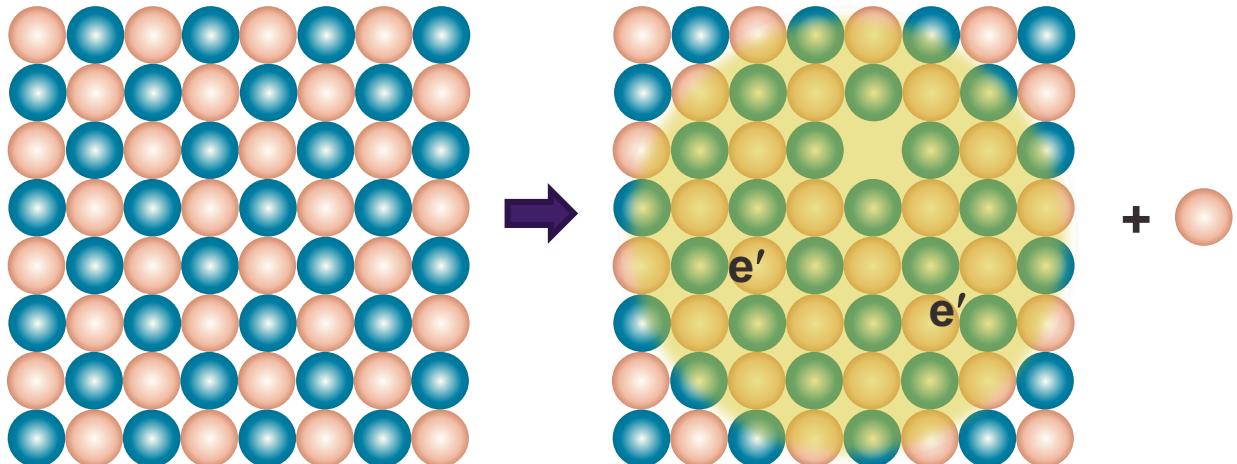
We wish to **define** the oxygen vacancy and **calculate** its energy of formation



$$\Delta_{red}G = \frac{1}{\delta} [\mu_{MO_{1-\delta}} - \mu_{MO}] + \mu_O + 2E_F$$

$$\mu_O = \frac{1}{2}\mu_{O_2}$$

$$\mu_{e^-} = E_F$$



From Energetics to Concentration

$$\Delta_{red}G = \frac{1}{\delta} \left[\underline{\mu_{MO_{1-\delta}}} - \mu_{MO} \right] + \mu_O + 2E_F$$

$$\mu_{MO_{1-\delta}} = h_{MO_{1-\delta}} - Ts_{MO_{1-\delta}}^{non-config} - Ts_{MO_{1-\delta}}^{config}$$

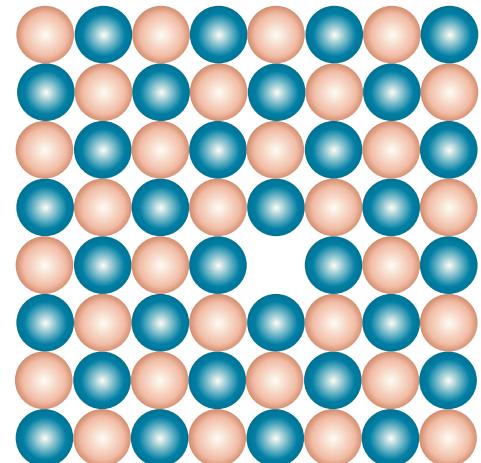
$$\Delta_{red}G = \frac{1}{\delta} \left[\mu_{MO_{1-\delta}}^* - \mu_{MO} \right] + \mu_O + 2E_F - \frac{1}{\delta} Ts_{MO_{1-\delta}}^{config}$$

$$\equiv \Delta G_{V_O^{\bullet\bullet}}$$

$$S = R \ln \Omega$$

$$\underline{\Omega_{MO_{1-\delta}}} \approx (\chi_{V_O^{\bullet\bullet}})^{-\delta}$$

1/ δ moles of MO



$$\equiv \boxed{\mu_{MO_{1-\delta}}^*} - Ts_{MO_{1-\delta}}^{config}$$

at equilibrium

$$\Delta_{red}G = 0 \quad \Rightarrow \Delta G_{V_O^{\bullet\bullet}} = \frac{1}{\delta} \underline{Ts_{MO_{1-\delta}}^{config}}$$

$$\Omega = \exp\left(\frac{S}{R}\right) \quad (\chi_{V_O^{\bullet\bullet}})^{-\delta} = \exp\left(\frac{\delta \Delta G_{V_O^{\bullet\bullet}}}{RT}\right)$$

$$\chi_{V_O^{\bullet\bullet}} = \exp\left(\frac{-\Delta G_{V_O^{\bullet\bullet}}}{RT}\right)$$

From Energetics to Concentrations

$$\chi_{V_O^{\bullet\bullet}} = \exp\left(\frac{-\Delta G_{V_O^{\bullet\bullet}}}{RT}\right)$$

$$\Delta G_{V_O^{\bullet\bullet}} \equiv \frac{1}{\delta} [\mu_{MO_{1-\delta}}^* - \mu_{MO}] + \mu_O + 2E_F$$

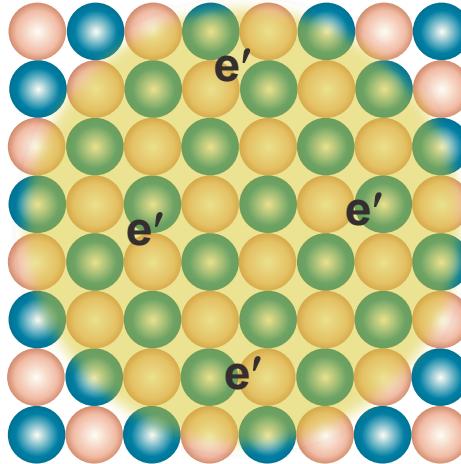
Vacancy concentration depends on **Fermi energy**, as well as on oxygen chemical potential

Express $\Delta G_{V_O^{\bullet\bullet}}$ relative to a reference state

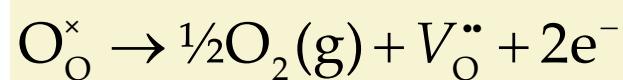
$$\Delta G_{V_O^{\bullet\bullet}}^0 \equiv \frac{1}{\delta} [\mu_{MO_{1-\delta}}^* - \mu_{MO}] + \mu_O^0 + 2E_F^0$$

$$\mu_{MO_{1-\delta}}^* \approx \mu_{MO_{1-\delta}}^{*,0} \quad \mu_{MO} \approx \mu_{MO}^0$$

$$\Delta G_{V_O^{\bullet\bullet}} = \Delta G_{V_O^{\bullet\bullet}}^0 + (\mu_O - \mu_O^0) + 2(E_F - E_F^0)$$



Connect to Defect Chemical Reaction

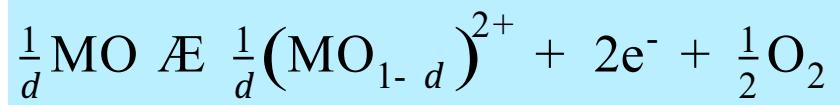


complete entropy

$$\mu_\text{O} = \frac{1}{2}\mu_{\text{O}_2} \quad \mu_{\text{e}^-} = E_\text{F}$$

$$\Delta_{red}g^0 = \mu_{\text{V}_\text{O}^{..}}^0 - \mu_{\text{O}_\text{O}^x}^0 + \mu_\text{O}^0 + 2E_\text{F}^0 = -\left[\Delta\bar{H}_\text{O}^0 - T(\Delta\bar{S}_\text{O}^0 - R \ln(\chi_{\text{V}_\text{O}^{..}} \chi_{\text{e}^-}^2)) \right]$$

excludes
configurational
entropy



$$\Delta G_{\text{V}_\text{O}^{..}}^0 = \frac{1}{\delta} \left[\mu_{\text{MO}_{1-\delta}}^{*,0} - \mu_{\text{MO}}^0 \right] + \mu_\text{O}^0 + 2E_\text{F}^0 \quad \text{also excludes configurational entropy}$$

Recognize $\frac{1}{\delta} \left[\mu_{\text{MO}_{1-\delta}}^{*,0} \right] = \mu_{\text{V}_\text{O}^{..}}^0 \quad \frac{1}{\delta} \left[\mu_{\text{MO}}^0 \right] = \mu_{\text{O}_\text{O}^x}^0 \Rightarrow \Delta G_{\text{V}_\text{O}^{..}}^0 = \Delta_{red}g^0$ by extension

$$\Delta G_{\text{V}_\text{O}^{..}} = \Delta_{red}g$$

$\Delta G_{\text{V}_\text{O}^{..}}, \Delta_{red}g$ depend on $E_\text{F}, p\text{O}_2$

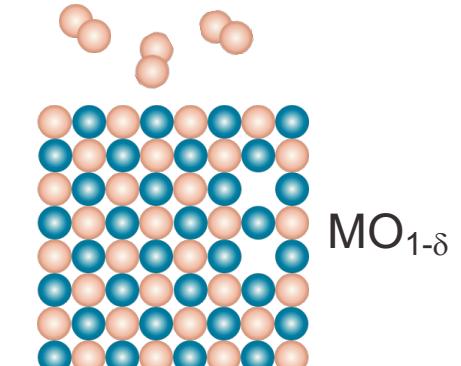
$\Delta G_{\text{V}_\text{O}^{..}}^0, \Delta_{red}g^0$ are fixed

Comparing Approaches

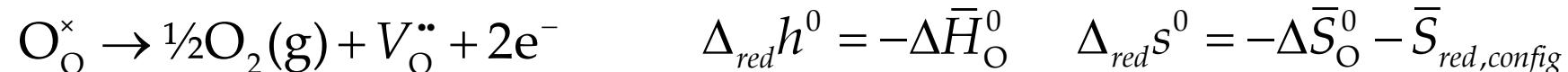
Macroscopic thermodynamics

$$\mu_O(T) - \mu_O^0(T) = \Delta \bar{G}_O^0 = RT \ln(\hat{p}_{O_2}^{1/2}(\delta)) = \Delta \bar{H}(O)^0 - T \Delta \bar{S}(O)^0$$

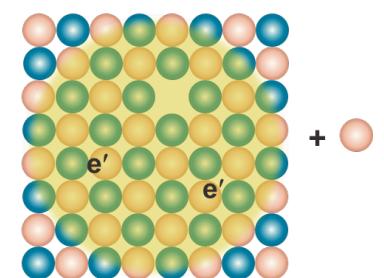
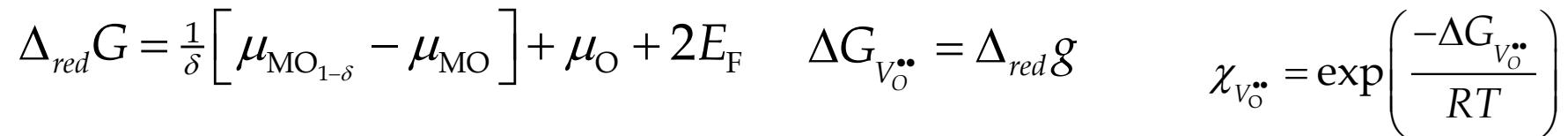
invert to solve for δ (T, p_{O_2})



Point defect chemical reaction



Point defect formation



entropy argument

Lecture Outline

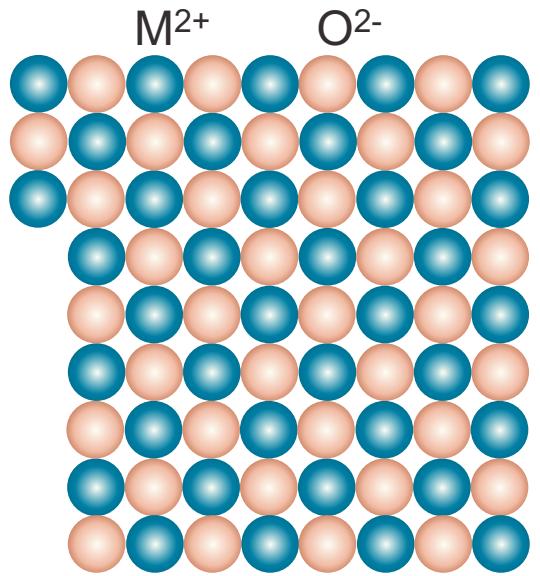
Thermodynamics of defect formation

- Macroscopic thermodynamic approach
 - Gas and solid state in equilibrium
 - Experimental methods
- Microscopic thermodynamics
 - Reduction/oxidation reaction
- Microscopic point defects
 - Energetics of defect formation
- • Brouwer diagrams – Defect concentrations



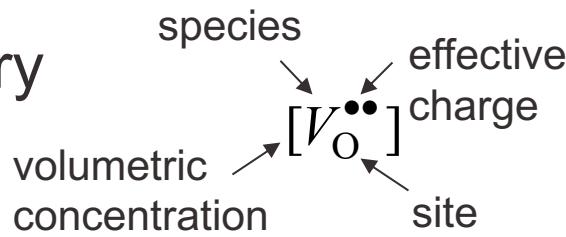
Treatment of Defect Concentrations

Formal Defect Chemistry



Energetics independent
of E_F and pO_2

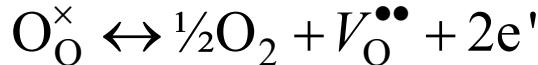
Typically one dominates



' negative, • positive, × neutral

$$\exp\left(\frac{-\Delta_{rxn}g^0}{RT}\right) = K_{eq} = \left(\frac{a_{p1}^{v_{p1}} a_{p2}^{v_{p2}} a_{p3}^{v_{p3}} \dots}{a_{r1}^{v_{r1}} a_{r2}^{v_{r2}} a_{r3}^{v_{r3}} \dots} \right)$$

Reduction



$$K_{red} = \left(\frac{\hat{p}_{O_2}^{1/2} \chi_{V_O^{\bullet\bullet}} \chi_{e^-}^2}{\chi_{O_O^{\times}}} \right) \approx \hat{p}_{O_2}^{1/2} \chi_{V_O^{\bullet\bullet}} \chi_{e^-}^2$$

Schottky defect formation



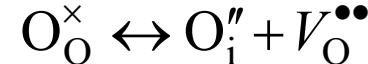
$$K_{Sch} = \left(\frac{\chi_{V_M''} \chi_{V_O^{\bullet\bullet}}}{\chi_{M_M^{\times}} \chi_{O_O^{\times}}} \right) \approx \chi_{V_M''} \chi_{V_O^{\bullet\bullet}}$$

Frenkel cation defect



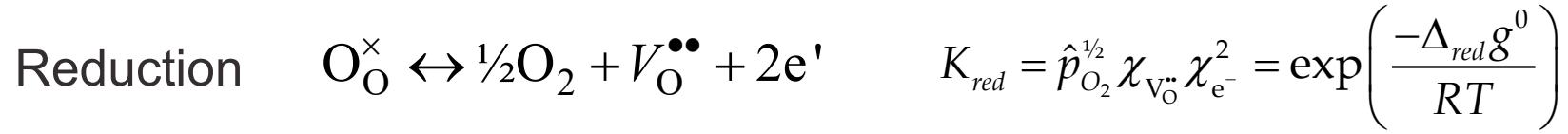
$$K_{F,C} = \left(\frac{\chi_{V_M''} \chi_{M_i^{\bullet\bullet}}}{\chi_{M_M^{\times}}} \right) \approx \chi_{V_M''} \chi_{M_i^{\bullet\bullet}}$$

Frenkel anion defect

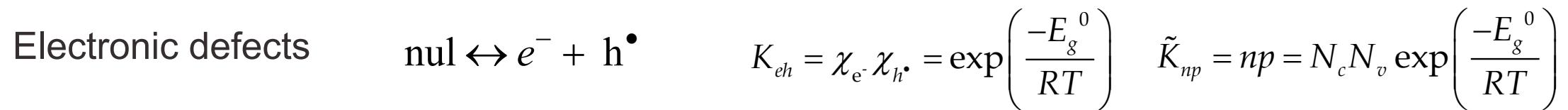


$$K_{F,A} = \left(\frac{\chi_{O_i''} \chi_{V_O^{\bullet\bullet}}}{\chi_{O_O^{\times}}} \right) \approx \chi_{O_i''} \chi_{V_O^{\bullet\bullet}}$$

Treatment of Defect Concentrations



has units



4 unknowns: $\chi_{O_i''}$ $\chi_{V_O^{\bullet\bullet}}$ χ_{e^-} χ_{h^\bullet} fractional concentrations volumetric concentrations, [], n, p

Additional equation from electroneutrality constraint: $\sum_i q_i c_i = 0$ $2[V_O^{\bullet\bullet}] + p = 2[O_i''] + n$

Wide band gap ionic material (electrolyte) at moderate pO_2 : n, p are low $2[V_O^{\bullet\bullet}] = 2[O_i'']$

Brouwer Diagram of Defect Concentrations

Take equilibrium constants to be known, evaluate defect concentrations as $f(pO_2)$ at a given temperature

$$2[V_O^{\bullet\bullet}] + p = 2[O_i''] + n$$

$$\tilde{K}_{red} = \hat{p}_{O_2}^{1/2} [V_O^{\bullet\bullet}] n^2 \quad \tilde{K}_{F,A} = [V_O^{\bullet\bullet}] [O_i''] \quad \tilde{K}_{np} = np$$

Moderate pO_2 $[V_O^{\bullet\bullet}] = [O_i'']$

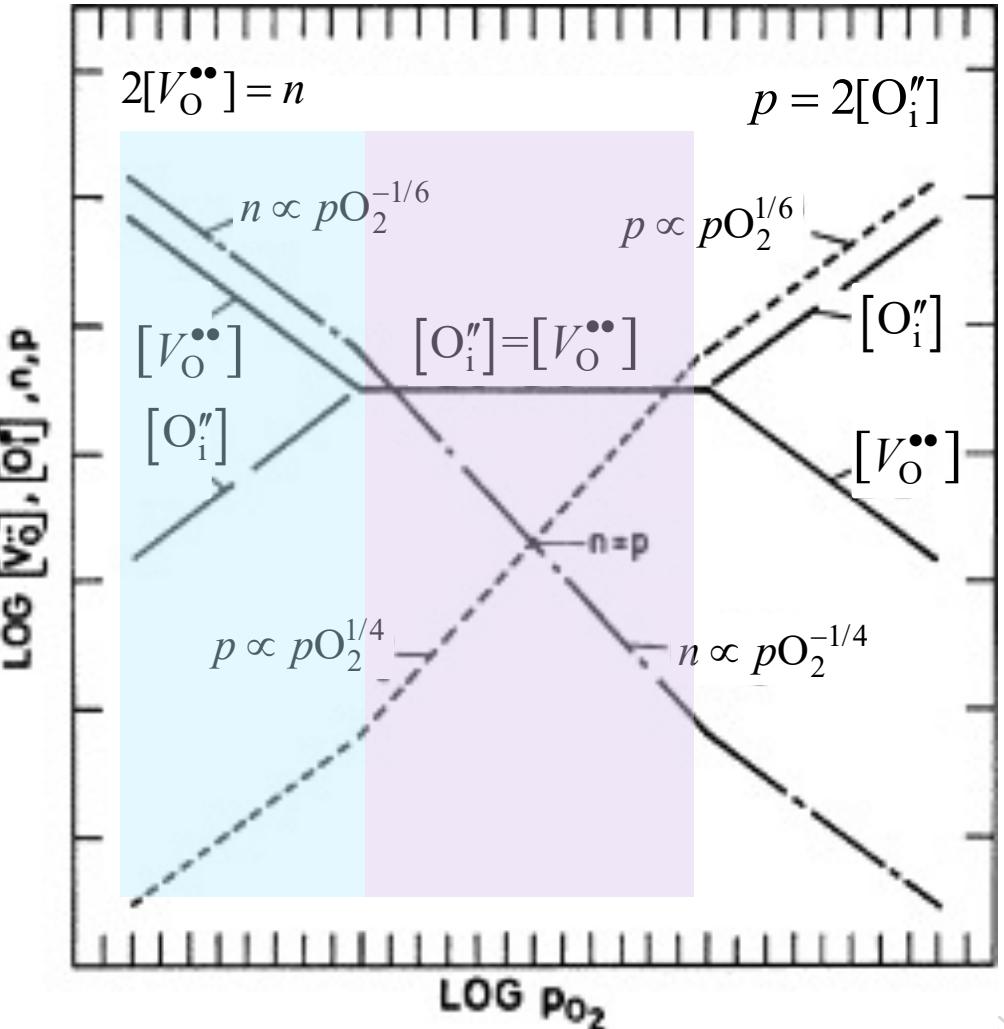
$$\Rightarrow \tilde{K}_{F,A} = [V_O^{\bullet\bullet}]^2 \quad \Rightarrow [V_O^{\bullet\bullet}] = (\tilde{K}_{F,A})^{1/2} = const$$

$$\Rightarrow \tilde{K}_{red} / const = \hat{p}_{O_2}^{1/2} n^2 \quad \Rightarrow n \propto \hat{p}_{O_2}^{-1/4}$$

$$p = \tilde{K}_{np} / n \quad \Rightarrow p \propto \hat{p}_{O_2}^{1/4}$$

Low pO_2 $2[V_O^{\bullet\bullet}] = n \quad \Rightarrow \tilde{K}_{red} = \hat{p}_{O_2}^{1/2} 4[V_O^{\bullet\bullet}]^3$

$$\Rightarrow [V_O^{\bullet\bullet}], n \propto \hat{p}_{O_2}^{-1/6} \quad \tilde{K}_{F,A} \Rightarrow [O_i''] \propto \hat{p}_{O_2}^{1/6} \quad \tilde{K}_{np} \Rightarrow p \propto \hat{p}_{O_2}^{1/6}$$



Small Band-gap Semiconductor

$$2[V_O^{\bullet\bullet}] + p = 2[O_i''] + n$$

$$\tilde{K}_{red} = \hat{p}_{O_2}^{1/2} [V_O^{\bullet\bullet}] n^2 \quad \tilde{K}_{F,A} = [V_O^{\bullet\bullet}] [O_i''] \quad \tilde{K}_{np} = np$$

Moderate pO_2 $p = n$

$$\Rightarrow \tilde{K}_{np} = n^2 \Rightarrow n = (\tilde{K}_{np})^{1/2} = const$$

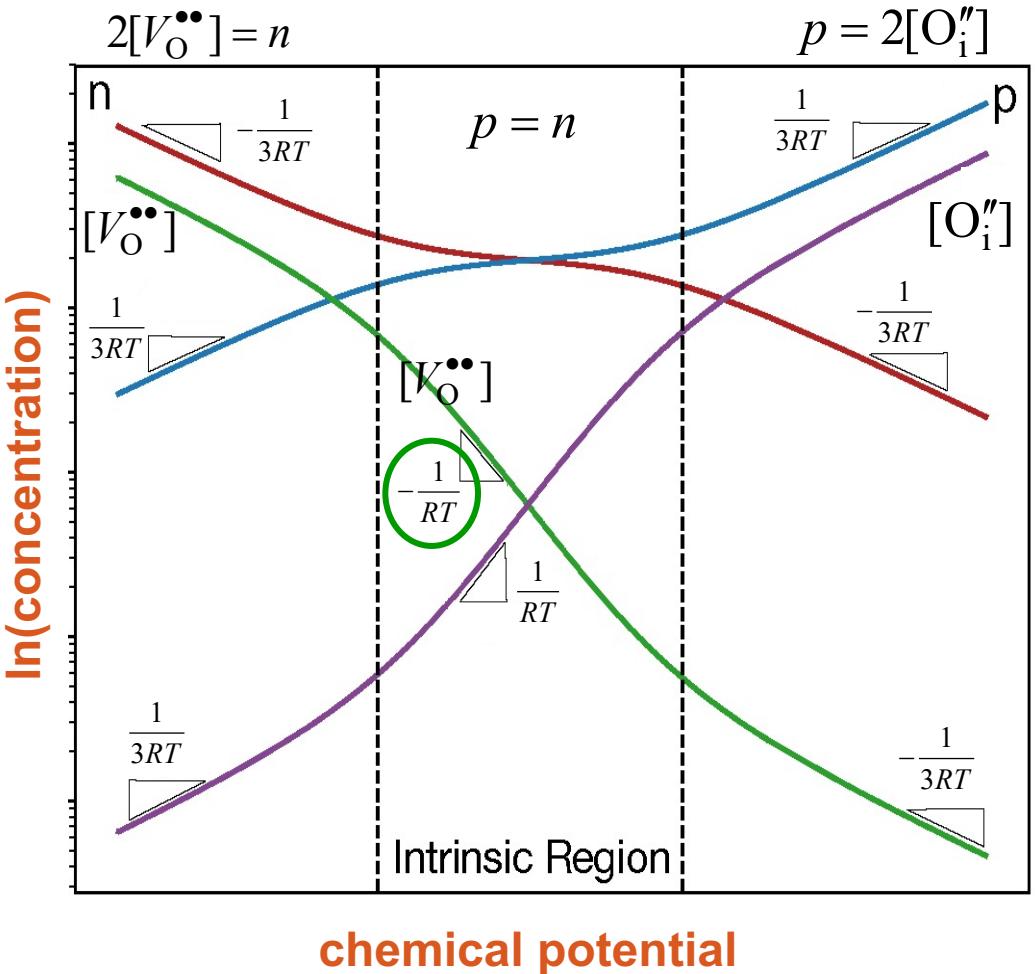
$$\Rightarrow \tilde{K}_{red} / \tilde{K}_{np} = \hat{p}_{O_2}^{1/2} [V_O^{\bullet\bullet}] = const \quad \ln[V_O^{\bullet\bullet}] = \ln(\hat{p}_{O_2}^{-1/2}) + const$$

$$\ln[V_O^{\bullet\bullet}] = \frac{-1}{RT} (RT \ln \hat{p}_{O_2}^{1/2}) + const$$

Low pO_2 $2[V_O^{\bullet\bullet}] = n \Rightarrow \tilde{K}_{red} = \hat{p}_{O_2}^{1/2} 4[V_O^{\bullet\bullet}]^3$

$$\Rightarrow [V_O^{\bullet\bullet}], n \propto \hat{p}_{O_2}^{-1/6} \Rightarrow \ln[V_O^{\bullet\bullet}] = \frac{-1}{3RT} (RT \ln \hat{p}_{O_2}^{1/2}) + const$$

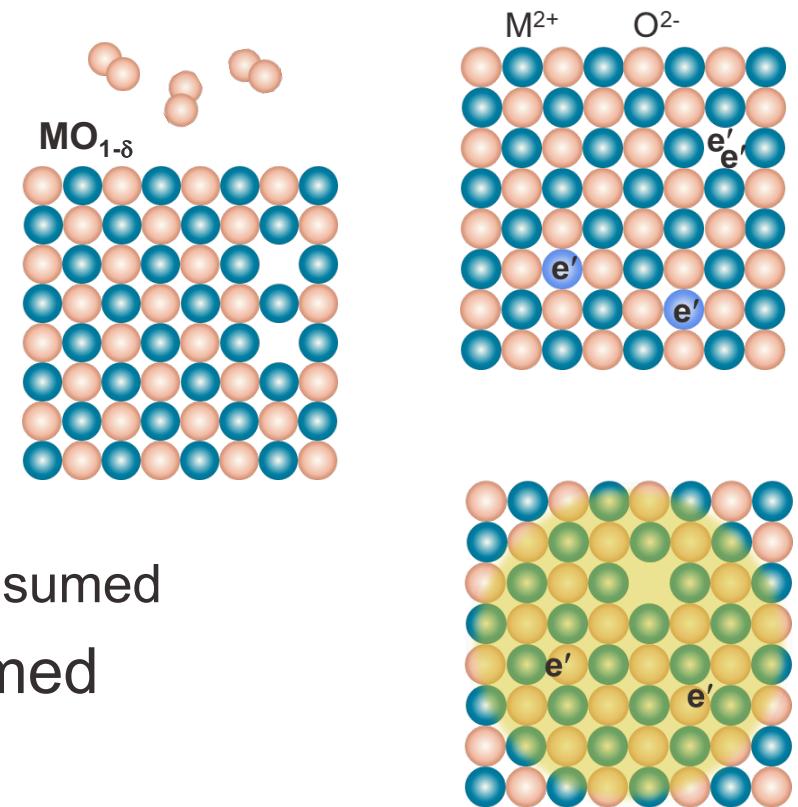
Courtesy G. J. Snyder and S. Anand



$$\mu_O(T) = \mu_O^0(T) + RT \ln(\hat{p}_{O_2}^{1/2})$$

Summary

- Defect formation in ionic solids and in compound semiconductors are analogous processes
- Language used to describe them is distinct
 - You now have the Rosetta stone for translating
- Macroscopic chemical view
 - Completely defect agnostic
- Point defect chemical reactions
 - Require site, mass and charge balance
- Defect formation energies
 - Assume charged defect, with electrons released/consumed
- With energetics known & form of entropy assumed
 - Can compute defect concentrations as $f(\mu, T)$



CONGRATULATIONS!!

You've made it through a tough lecture at the end of a long day!

I wish you all the success in the world as you navigate these challenging times!

Applying to US graduate schools in STEM fields

Virtual Webinar

August 13, 2021
4 PM Addis Ababa
US: 6 AM PST / 7 AM MST / 8 AM CST / 9 AM EST

Zoom Registration link:
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Incoming Professor of Materials
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